

MMBTH10LT1G, NSVMMBTH10LT1G, MMBTH10LT3G, MMBTH10-4LT1G



ON Semiconductor®

<http://onsemi.com>

VHF/UHF Transistor

NPN Silicon

Features

- AEC-Q101 Qualified and PPAP Capable
- NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc

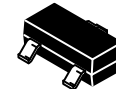
THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

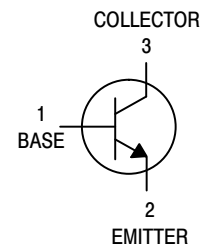
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.
2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina

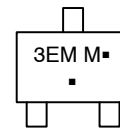
*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.



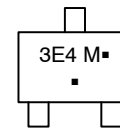
SOT-23 (TO-236)
CASE 318
STYLE 6



MARKING DIAGRAMS



MMBTH10LT1G,
NSVMMBTH10LT1G



MMBTH10-04LT1G

3EM, 3E4 = Specific Device Code
M = Date Code*
▪ = Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping†
MMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
NSVMMBTH10LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel
MMBTH10LT3G	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBTH10-4LT1G	SOT-23 (Pb-Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MMBTH10LT1G, NSVMMBTH10LT1G, MMBTH10LT3G, MMBTH10-4LT1G

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage (I _C = 1.0 mA _{dc} , I _B = 0)	V _{(BR)CEO}	25	-	-	V _{dc}
Collector-Base Breakdown Voltage (I _C = 100 μA _{dc} , I _E = 0)	V _{(BR)CBO}	30	-	-	V _{dc}
Emitter-Base Breakdown Voltage (I _E = 10 μA _{dc} , I _C = 0)	V _{(BR)EBO}	3.0	-	-	V _{dc}
Collector Cutoff Current (V _{CB} = 25 V _{dc} , I _E = 0)	I _{CBO}	-	-	100	nA _{dc}
Emitter Cutoff Current (V _{EB} = 2.0 V _{dc} , I _C = 0)	I _{EBO}	-	-	100	nA _{dc}

ON CHARACTERISTICS

DC Current Gain (I _C = 4.0 mA _{dc} , V _{CE} = 10 V _{dc}) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G	h _{FE}	60 120	- -	- 240	-
Collector-Emitter Saturation Voltage (I _C = 4.0 mA _{dc} , I _B = 0.4 mA _{dc})	V _{CE(sat)}	-	-	0.5	V _{dc}
Base-Emitter On Voltage (I _C = 4.0 mA _{dc} , V _{CE} = 10 V _{dc})	V _{BE}	-	-	0.95	V _{dc}

SMALL-SIGNAL CHARACTERISTICS

Current-Gain - Bandwidth Product (I _C = 4.0 mA _{dc} , V _{CE} = 10 V _{dc} , f = 100 MHz) MMBTH10LT1G, NSVMMBTH10LT1G MMBTH10-4LT1G	f _T	650 800	- -	- -	MHz
Collector-Base Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{cb}	-	-	0.7	pF
Common-Base Feedback Capacitance (V _{CB} = 10 V _{dc} , I _E = 0, f = 1.0 MHz)	C _{rb}	-	-	0.65	pF
Collector Base Time Constant (I _C = 4.0 mA _{dc} , V _{CB} = 10 V _{dc} , f = 31.8 MHz)	rb'C _c	-	-	9.0	ps

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mA dc}$, $T_A = 25^\circ\text{C}$)

y_{ib} , INPUT ADMITTANCE

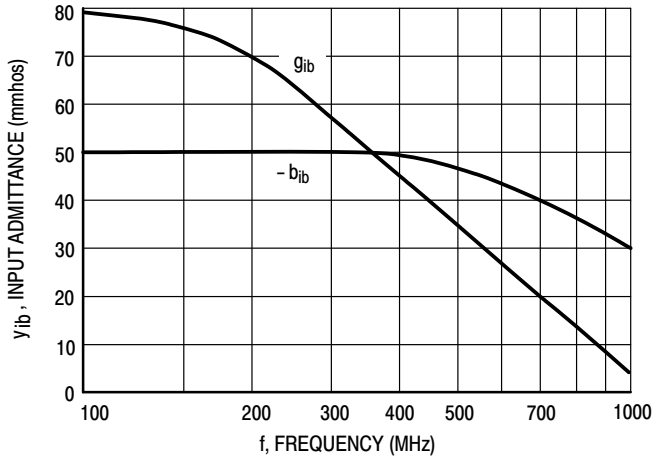


Figure 1. Rectangular Form

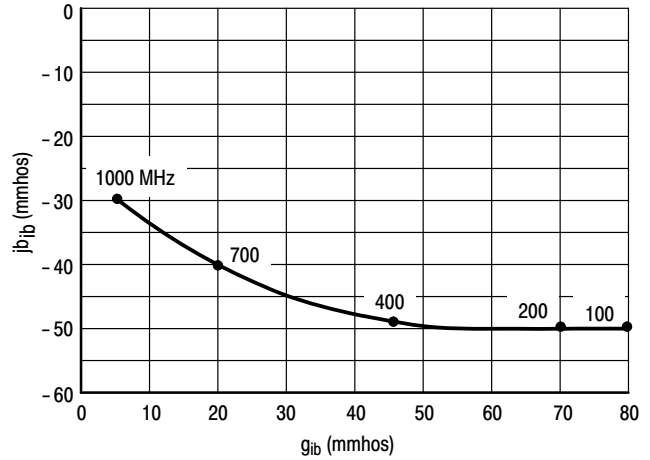


Figure 2. Polar Form

y_{fb} , FORWARD TRANSFER ADMITTANCE

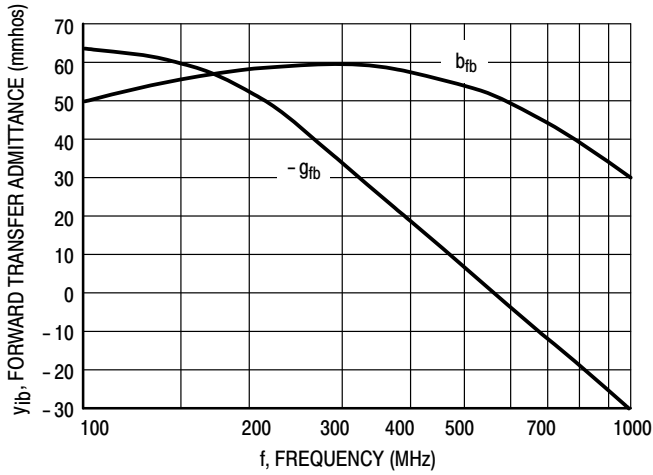


Figure 3. Rectangular Form

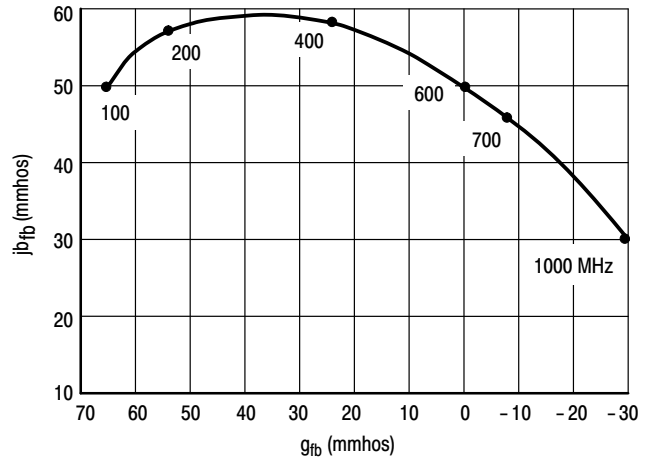


Figure 4. Polar Form

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mAdc}$, $T_A = 25^\circ\text{C}$)

y_{rb} , REVERSE TRANSFER ADMITTANCE

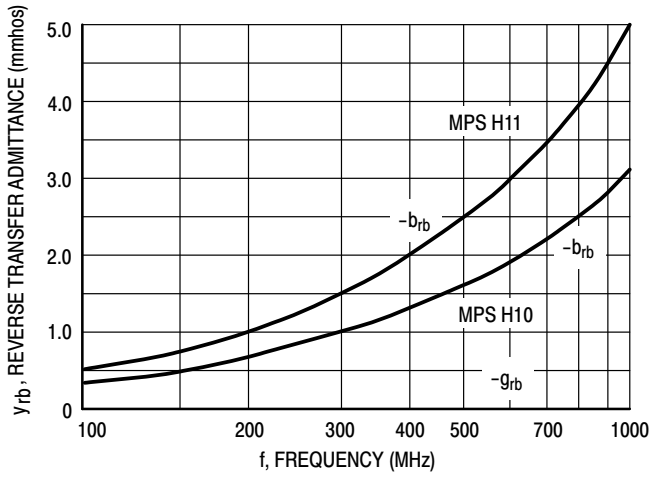


Figure 5. Rectangular Form

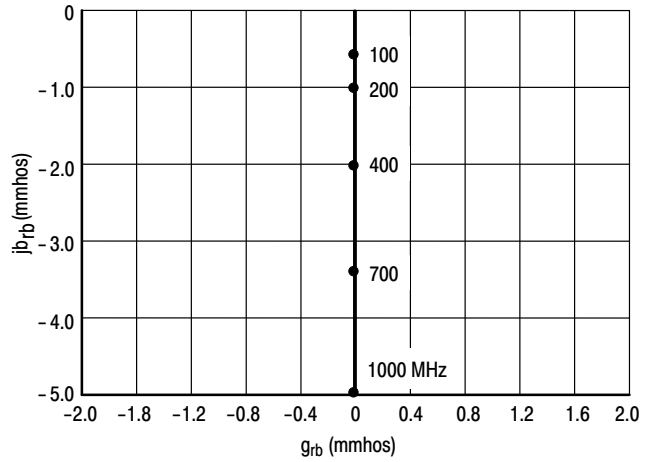


Figure 6. Polar Form

y_{ob} , OUTPUT ADMITTANCE

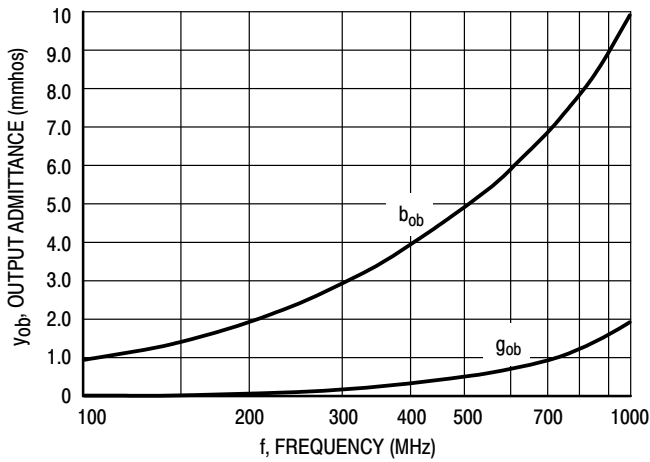


Figure 7. Rectangular Form

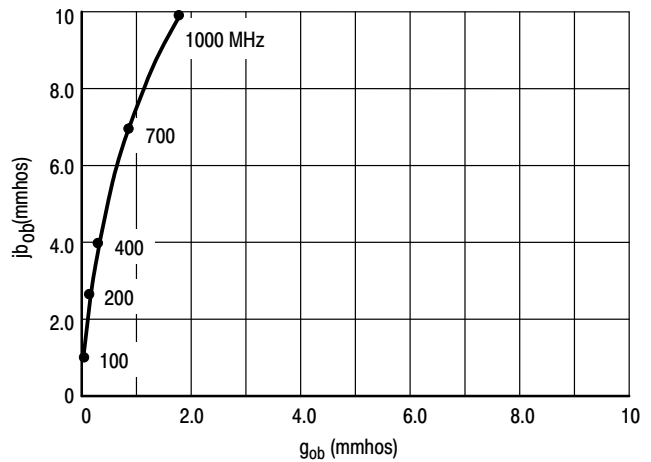
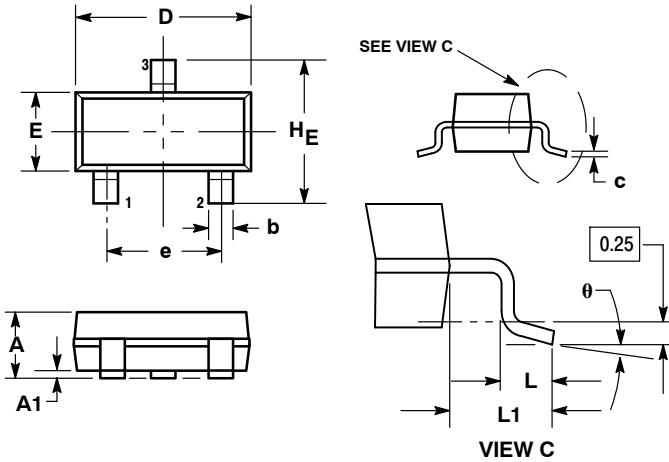


Figure 8. Polar Form

MMBTH10LT1G, NSVMMBTH10LT1G, MMBTH10LT3G, MMBTH10-4LT1G

PACKAGE DIMENSIONS

SOT-23 (TO-236)
CASE 318-08
ISSUE AP



NOTES:

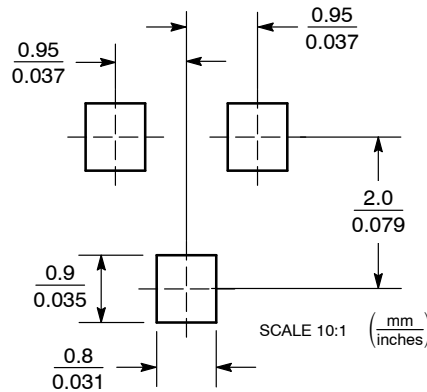
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
HE	2.10	2.40	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT



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